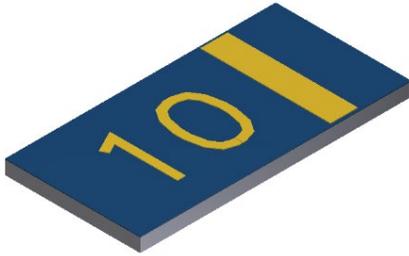


**Surface Mount Attenuator
10 Watts, 10dB**



The XRA10AA10SES is a high performance Aluminum Nitride (AlN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). It is designed particularly for LTE and 5G wireless communication frequency bands. The high power handling makes the part ideal for inter-stage matching, directional couplers, and for use in isolators. The attenuator is also RoHS compliant!

Features:

- RoHS Compliant
- 10 Watts
- Low Cost
- DC – 6.0GHz
- AlN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

General Specifications

Resistive Element	Thick film
Substrate	AlN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +150°C (see de rating chart)

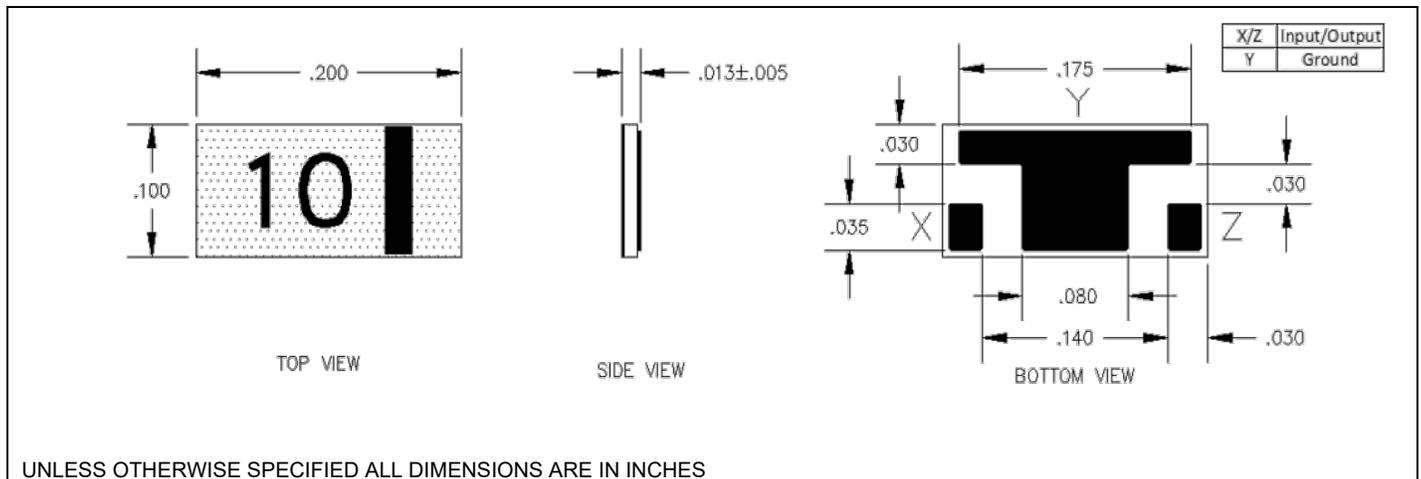
Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. **All dimensions in inches.**

Electrical Specifications

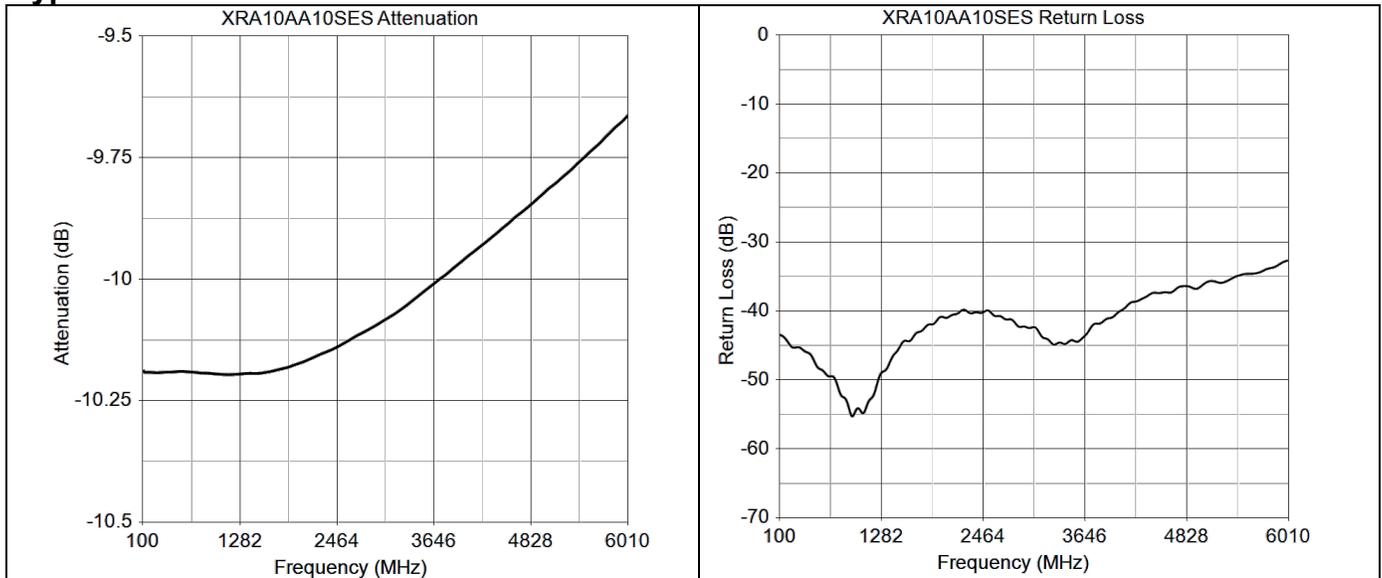
Attenuation Value:	10dB \pm 0.5 dB
Power:	10 Watts
Frequency Range:	DC – 6.0GHz
Input Return Loss:	20dB

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

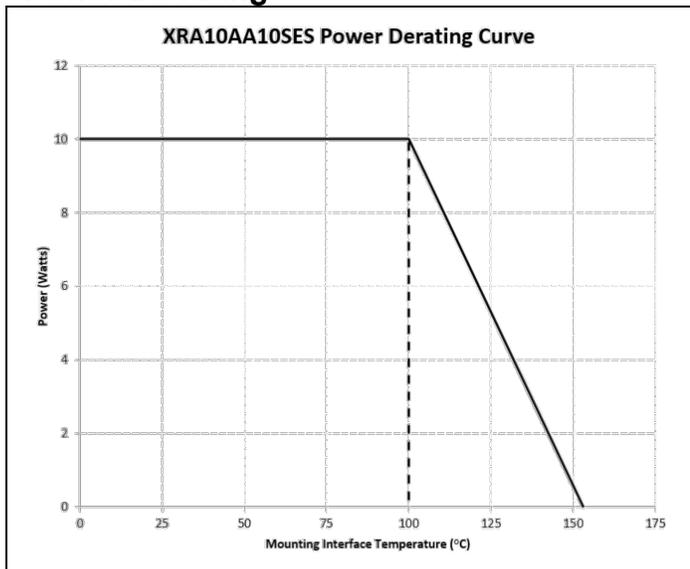
Outline Drawing



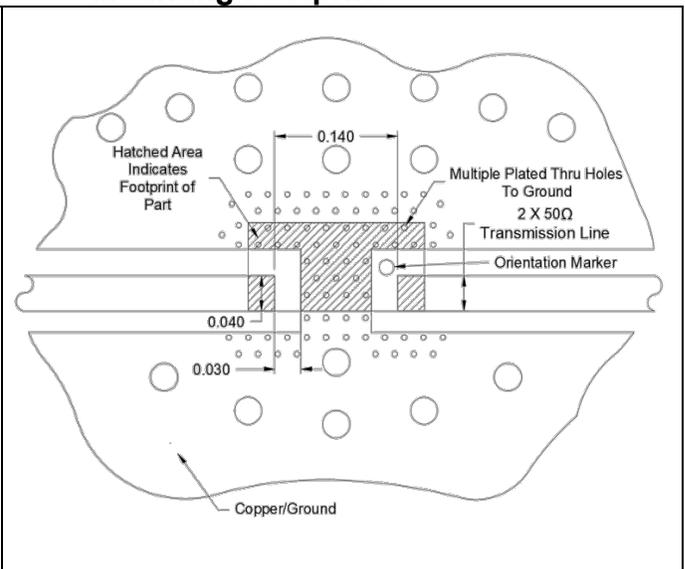
Typical Performance:



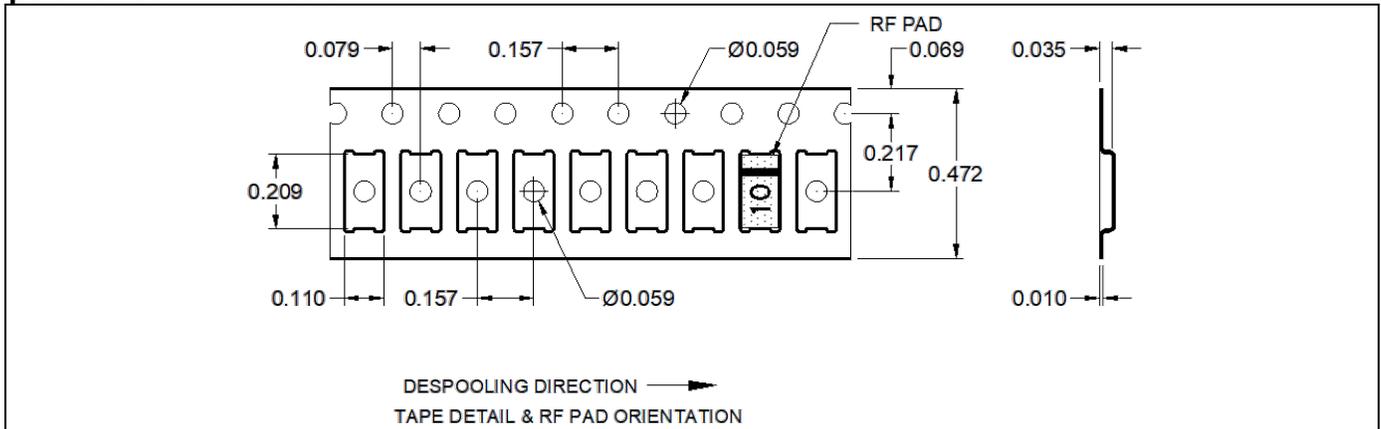
Power De-rating



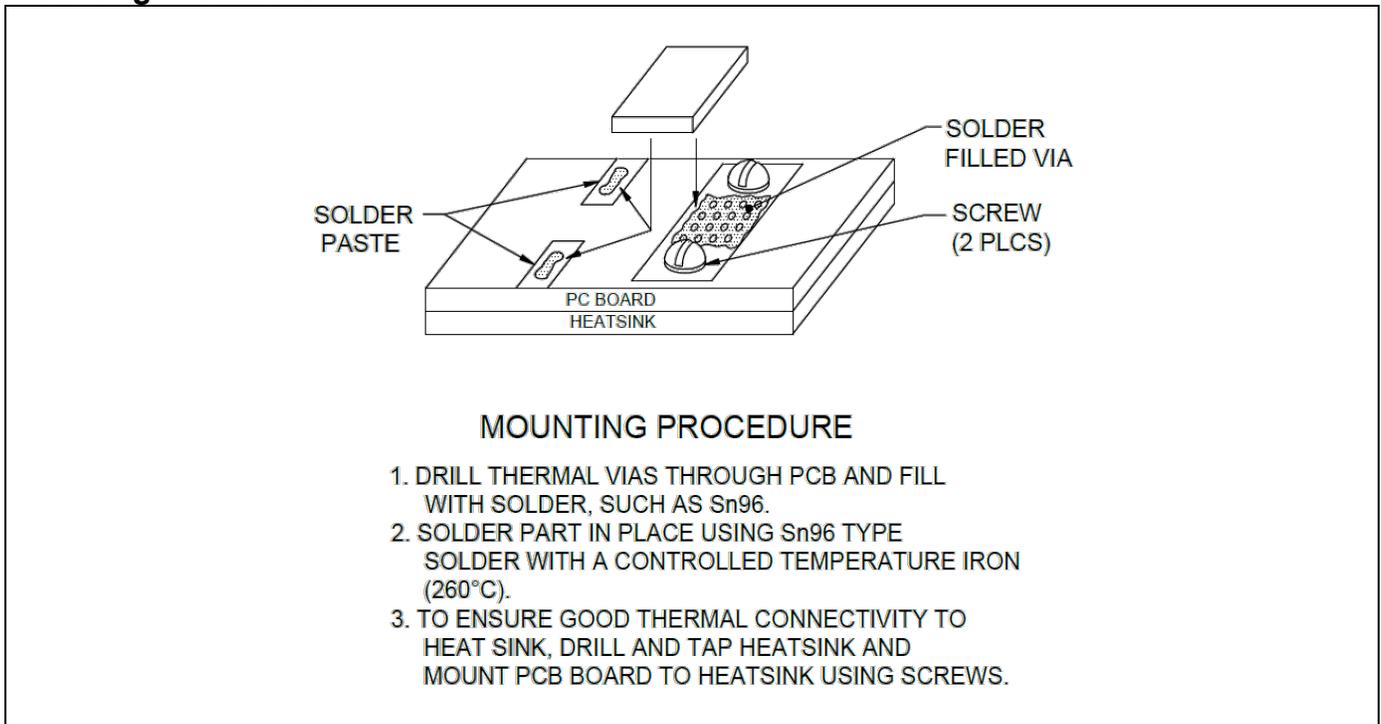
Mounting Footprint



Tape and reel information:



Mounting Procedure:



Contact us:
rf&s_support@ttm.com